





### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Package	Max I <sub>D</sub> T <sub>A</sub> = +25°C	
100V	125mΩ @ V <sub>GS</sub> = 10V	TO252	6.4A	
1000	150mΩ @ V <sub>GS</sub> = 6V	(DPAK)	5.8A	

### **Features**

- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

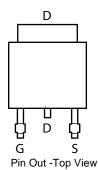
- DC-DC Converters
- · Power Management Functions
- Disconnect Switches
- Motor Control

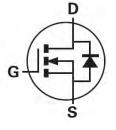
### **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)









**Equivalent Circuit** 

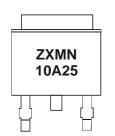
### Ordering Information (4 & 5)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A25KTC	ZXMN10A25	13	16	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For Packaging Details, go to our website at http://www.diodes.com.
- 5. Products with Q-suffix are automotive grade. Automotive products are electrical and thermal the same as the commercial, except where specified.

## **Marking Information**



ZXMN10A25 = Product Type Marking Code





### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Ch	naracteristic		Symbol	Value	Unit
Drain-Source voltage			$V_{DSS}$	100	V
Gate-Source voltage			V <sub>GS</sub>	±20	V
		(Note 7)		6.4	
Continuous Drain current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	I <sub>D</sub>	5	Α
		(Note 6)		4.2	
Pulsed Drain current (Note 8)		I <sub>DM</sub>	21	A	
Continuous Source current (Body diode) (Note 7)			IS	10	A
Pulsed Source current (Body diode) (Note 8)			I <sub>SM</sub>	21	A

### **Thermal Characteristics**

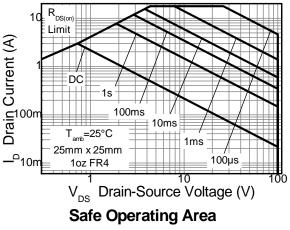
Characteristic	Symbol	Value	Unit	
	(Note 6)		4.25 34	
Power dissipation Linear derating factor	(Note 7)	P <sub>D</sub>	9.85 78.7	W mW/°C
	(Note 9)		2.11 16.8	
	(Note 6)		29.4	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	12.7	2011
	(Note 9)		59.1	°C/W
Thermal Resistance, Junction to Lead	(Note 10)	$R_{ heta JL}$	1.43	
Operating and storage temperature range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	

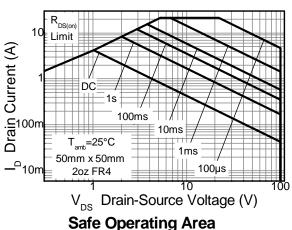
- 6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. For a device surface mounted on FR4 PCB measured at  $t \le 10$  sec.
- 8. Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.

  9. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 10. Thermal resistance from junction to solder-point (at the end of the drain lead).



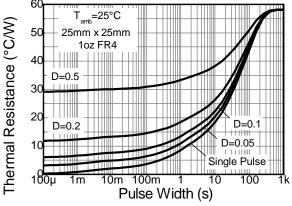
### **Thermal Characteristics**

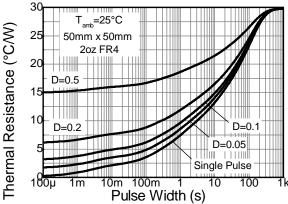






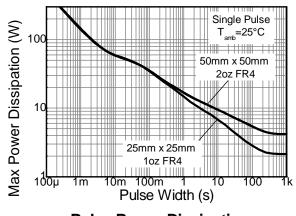


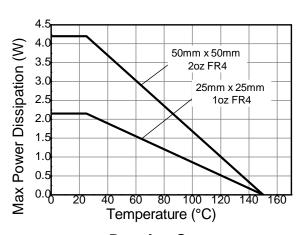




# **Transient Thermal Impedance**

**Transient Thermal Impedance** 





**Pulse Power Dissipation** 

**Derating Curve** 





# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	on
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100			V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	0.5	μΑ	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(th)</sub>	2.0	_	4.0	V	$I_D = 250 \mu A, V_{DS} = V_{GS}$	
Static Drain Source On Decistores (Note 14)				125	•	$V_{GS} = 10V, I_D = 3.2A$	
Static Drain-Source On-Resistance (Note 11)	R <sub>DS (ON)</sub>	_	_	150	mΩ	$V_{GS} = 6V, I_D = 2.6A$	
Forward Transconductance (Notes 11 & 12)	<b>g</b> fs	_	7.3	_	S	$V_{DS} = 15V, I_{D} = 2.9A$	
Diode Forward Voltage (Note 11)	$V_{SD}$	_	0.85	0.95	V	$I_S = 3.2A$ , $V_{GS} = 0V$ , $T_J = +25$ °C	
Reverse recovery time (Note 12)	t <sub>rr</sub>		40.5	_	ns	$I_S = 2.9A$ , di/dt = 100A/ $\mu$ s	
Reverse recovery charge (Note 12)	Qrr	_	62	_	nC	T <sub>J</sub> = +25°C	
DYNAMIC CHARACTERISTICS (Note 12)							
Input Capacitance	Ciss	_	859	_	pF		
Output Capacitance	Coss	_	57.3	_	pF	$V_{DS} = 50V, V_{GS} = 0V$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	33	_	pF	f = 1MHz	
Total Gate Charge (Note 13)	Qq	_	9.6	_	nC	$V_{GS} = 5V$	
Total Gate Charge (Note 13)	Qq	_	17.16	_	nC	V <sub>DS</sub> = 50V I <sub>D</sub> = 2.9A	
Gate-Source Charge (Note 13)	Qgs	_	3.77	_	nC		
Gate-Drain Charge (Note 13)	$Q_{gd}$	_	5.36	_	nC		
Turn-On Delay Time (Note 13)	t <sub>D(on)</sub>	_	4.9	_	ns	$V_{DD} = 50V$ , $V_{GS} = 10V$ $I_D = 1A$ , $R_G \cong 6.0\Omega$	
Turn-On Rise Time (Note 13)	tr	_	3.7	_	ns		
Turn-Off Delay Time (Note 13)	t <sub>D(off)</sub>	_	17.7	_	ns		
Turn-Off Fall Time (Note 13)	t <sub>f</sub>	_	9.4		ns		

Notes:

- 11. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
  12. For design aid only, not subject to production testing.
  13. Switching characteristics are independent of operating junction temperatures.

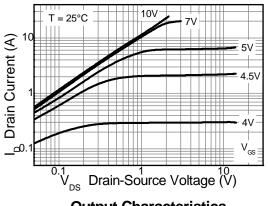


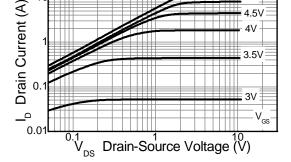
10V

4.5V

ZXMN10A25K

# **Typical Characteristics**

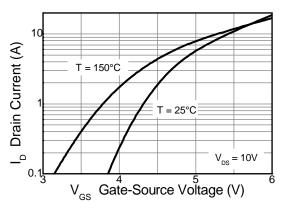


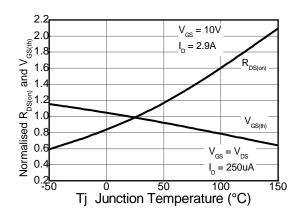


T = 150°C

### **Output Characteristics**

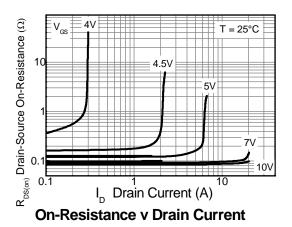
**Output Characteristics** 

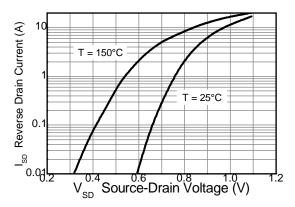




**Typical Transfer Characteristics** 

**Normalised Curves v Temperature** 

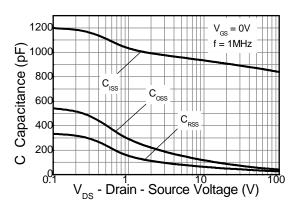




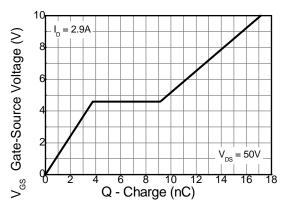
**Source-Drain Diode Forward Voltage** 



# **Typical Characteristics** (cont.)

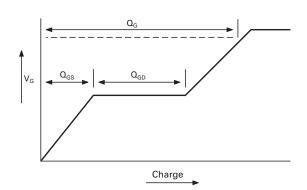


Capacitance v Drain-Source Voltage

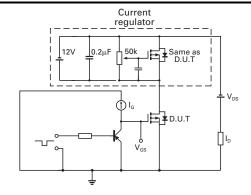


**Gate-Source Voltage v Gate Charge** 

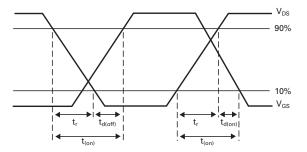
## **Test Circuits**



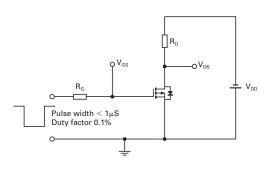
Basic gate charge waveform



Gate charge test circuit



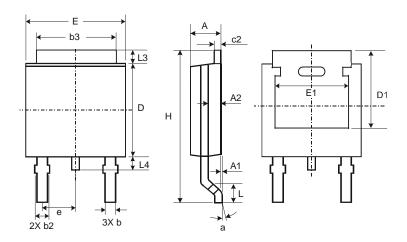
Switching time waveforms



Switching time test circuit

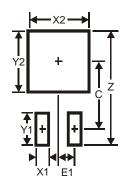


# **Package Outline Dimensions**



TO252					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A</b> 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	1	1		
е	-	_	2.286		
Е	6.45	6.70	6.58		
E1	4.32	_	_		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	_		
All	All Dimensions in mm				

# **Suggested Pad Layout**



Dimensions	Value (in mm)	
Z	11.6	
X1	1.5	
X2	7.0	
Y1	2.5	
Y2	7.0	
С	6.9	
E1	2.3	





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